

2814



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#100 Audit  
M. Brunson  
1/9/03

Applicant : Kusumoto, et al.      Art Unit :      2814  
Serial No.: 09/941,367      Examiner :      Theresa T. Doan  
Filed : August 28, 2001  
Title : METHOD FOR PRODUCING INSULATED GATE THIN FILM  
SEMICONDUCTOR DEVICE

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT

Responsive to the action mailed November 26, 2002,  
applicants elect the invention of Group I drawn to the  
embodiment of claims 1, 2, 9-10 and 17-20. The election is made  
without traverse.

Further, applicants wish to amend the application as  
follows:

In the claims:

Please amend claims 17-20 as follows:

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-- 17. A method according to any one of claims 1, 2, 9 and  
10, wherein said semiconductor layer comprises amorphous  
silicon.

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